

sub  
D1  
Circuit

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas;  
forming a gate electrode on said insulating film;  
introducing phosphorus into said first and second semiconductor islands; and  
introducing boron into said second semiconductor island,  
wherein a dose amount of said boron is larger than that of said phosphorus.

---

6. (Thrice Amended) A method for manufacturing a semiconductor device comprising the steps of:

sub  
D2  
Circuit

forming a semiconductor film comprising amorphous silicon over a substrate;  
crystallizing said semiconductor film by irradiating a laser light;  
patterning the crystallized semiconductor film to form first and second semiconductor islands;

forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition;

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas;

forming a gate electrode on said insulating film;

introducing phosphorus into said first and second semiconductor islands; and

introducing boron into said second semiconductor island,

wherein a dose amount of said boron is larger than that of said phosphorus.

---

sub  
D3  
Circuit

11. (Thrice Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;

crystallizing said semiconductor film by irradiating a laser light;

Sub D363  
Amended

patterning the crystallized semiconductor film to form first and second semiconductor islands;

forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition using TEOS;

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas;

forming a gate electrode on said insulating film;

introducing phosphorus into said first and second semiconductor islands; and

introducing boron into said second semiconductor island,

wherein a dose amount of said boron is larger than that of said phosphorus.

Sub D364  
Amended

30. (Thrice Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a crystalline semiconductor film over a substrate;

patterning the crystallized semiconductor film to form first and second semiconductor islands;

forming an insulating film comprising silicon oxide on each of said first and second semiconductor islands by a vapor phase deposition;

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas;

forming a gate electrode on said insulating film;

introducing phosphorus into said first and second semiconductor islands; and

introducing boron into said second semiconductor island,

wherein a dose amount of said boron is larger than that of said phosphorus.

Sub D365  
Amended

34. (Thrice Amended) A method for manufacturing a semiconductor device